SUPPLEMENTAL APPLICATION DA

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U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE der the Panerwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number. Attorney Docket Number 039.0075 Application Data Sheet 37 CFR 1.76 Application Number III Nitride Semiconductor Crystal and Manufacturing Method Thereof, III Nitride Semiconductor Device and Title of Invention Manufacturing Method Thereof, and Light Emitting Device The application data sheet is part of the provisional or nonprovisional application for which it is being submitted. The following form contains the bibliographic data arranged in a format specified by the United States Patent and Trademark Office as outlined in 37 CFR 1.76. This document may be completed electronically and submitted to the Office in electronic format using the Electronic Filing System (EFS) or the document may be printed and included in a paper filed application. Secrecy Order 37 CFR 5.2 Portions or all of the application associated with this Application Data Sheet may fall under a Secrecy Order pursuant to 37 CFR 5.2 (Paper filers only, Applications that fall under Secrecy Order may not be filed electronically.) Applicant Information: Applicant 1 Applicant Authority Olnventor OLegal Representative under 35 U.S.C. 117 Party of Interest under 35 U.S.C. 118 Prefix Given Name Middle Name **Family Name** Suffix Nakahata Mr. Seiji Active US Military Service Non US Residency Residence Information (Select One) US Residency Country Of Residence City Itami-shi Citizenship under 37 CFR 1.41(b) Mailing Address of Applicant: Address 1 Sumitomo Electric Industries, Ltd. Address 2 1-1 Koyakita 1-chome City Itami-shi, Hyogo State/Province **Postal Code** Countryi Japan Applicant 2 OLegal Representative under 35 U.S.C. 117 Applicant Authority Inventor Party of Interest under 35 U.S.C. 118 Suffix Middle Name **Family Name** Prefix Given Name Nakahata Mr Hideaki Non US Residency Active US Military Service Residence Information (Select One) US Residency Country Of Residence City Itami-shi Citizenship under 37 CFR 1.41(b) JP **Mailing Address of Applicant:** Sumitomo Electric Industries, Ltd. Address 1 1-1 Koyakita 1-chome Address 2 State/Province Itami-shi, Hyogo City **Postal Code** Country Japan **Applicant 3** Party of Interest under 35 U.S.C. 118 Applicant Authority Inventor OLegal Representative under 35 U.S.C. 117 Suffix **Family Name** Prefix **Given Name** Middle Name Uematsu Non US Residency Active US Military Service

US Residency

Country Of Residence

City

Itami-shi

Residence Information (Select One)

PTO/SB/14 (08-05)
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Application Data Sheet 37 CFR 1.				1 76	Attorney Docket Number		039.0	039.0075					
Appii	Application Data Chock of Oliver			1.70	Application Number			er	10	10/598,934			
Title of	Title of Invention III Nitride Semiconductor Crystal and Manufacturing Method Thereof, III Nitride Semiconductor Device and Manufacturing Method Thereof, and Light Emitting Device												
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	Applicant 6												
Applic	Applicant Authority • Inventor						.C. 118						
Prefix		ven Nar				N	Middle Name				Family Name		Suffix
Mr.	Tal	kao									Nakar	mura	
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City	City Itami-shi Country Of Residence JP												

Citizenship under 37 CFR 1.41(b) i

JP

PTO/SB/14 (08-05)
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Application D	Attorney Docket Number		039.0075					
Application D	Application Number		10/59	8,934				
Title of Invention			de Semiconductor Crystal and Manufacturing Method Thereof, III Nitride Semiconductor Device and incturing Method Thereof, and Light Emitting Device					
Mailing Address	of App	licant:						
Address 1		Sumitomo Electric Indus	stries, Ltd	l.				
Address 2		1-1 Koyakita 1-chome	1 Koyakita 1-chome					
City Itami-shi, Hyogo		30	>		State/Province			
Postal Code				Count	ryi Japan			
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Corresponde	ence l	nformation:						
		Number or complete see 37 CFR 1.33(a).	the Cor	respond	ence Infor	mation section	on below.	
An Address	is bein	g provided for the co	orrespo	ndence	Informatio	n of this appl	lication.	
Customer Numb	er	29453						
Email Address		jj@j-pat.jp	_				Add Email	Remove Email
Application I	nforn							
Title of the Inver	ntion	III Nitride Semicondu and Manufacturing N					of, III Nitride Se	miconductor Device
Attorney Docket Number			039.0075			tity Status C	laimed 🗌	
Application Type	•	Nonprovisional	Nonprovisional			-		
Subject Matter		Utility	Utility					
Suggested Class	s (if any				Sub Class (if any)			
Suggested Tech	nology	Center (if any)						
Total Number of	Drawin	g Sheets (if any)	11		Suggest	ed Figure for	Publication	(if any)
Publication Info	mation	•						
	•	cation (Fee required at				·		
Request Not to Publish. I hereby request that the attached application not be published under 35 U.S.C. 122(b) and certify that the invention disclosed in the attached application has not been and will not be the subject of an application filed in another country, or under a multilateral agreement, that requires publication at eighteen months after filing.								
this information in t Enter either C	ormation ne Applic ustomer	formation: should be provided for ation Data Sheet does not	ot constit	tute a pov Repre	er of attorne sentative	y in the applica Name section	ation (see 37 CF n below. If	
Please Select On	e :	Customer Number	. 10	US Pate	ent Practition	er US	Representative	e (37 CFR 11.9)
Customer Number	r	29453						

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Application Da	nta Sheet 37 CFR 1.76	Attorney Docket Number	039.0075		
Application Da	ila Sheel S/ CFK 1.70	Application Number	10/598,934		
Title of Invention	III Nitride Semiconductor Crys Manufacturing Method Thered		Thereof, III Nitride Semiconductor Device and		

Domestic Priority Information:

This section allows for the applicant to claim benefit under 35 U.S.C. 119(e), 120, 121, or 365(c). Providing this information in the application data sheet constitutes the specific reference required by 35 U.S.C. 119(e) or 120, and 37 CFR 1.78(a)(2) or CFR 1.78(a) (4), and need not otherwise be made part of the specification.							
Prior Application Status			Remove				
Application Number	Continuity Type	Prior Application Number	Filing Date (YYYY-MM-DD)				
Additional Domestic Priority D	oata may be generated wi	thin this form by selecting					

Foreign Priority Information:

This section allows for the applicant to claim benefit of foreign priority and to identify any prior foreign application for which priority is not claimed. Providing this information in the application data sheet constitutes the claim for priority as required by 35 U.S.C. 119(b) and 37 CFR 1.55(a).

	Remove				
Country i	Parent Filing Date (YYYY-MM-DD)	Priority Claimed			
APAN	2004-05-18	● Yes ○ No			
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Country i	Parent Filing Date (YYYY-MM-DD)	Priority Claimed			
APAN	2005-04-15	Yes No			
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Assignee Information:

100.9		_				
Providing this information of the CFR to have an as	n in the application data sheet signment recorded in the Off	t does not substitute for compliance vice.	vith any requirement of part 3 of Title 37			
Assignee 1	-					
If the Assignee is an C	rganization check here.	×				
Organization Name Sumitomo Electric Industries, Ltd.						
Mailing Address Info	rmation:					
Address 1	5-33 Kitahama 4-chon	5-33 Kitahama 4-chome, Chuo-ku				
Address 2						
City	Osaka	State/Province				
Country i JP		Postal Code	541-0041			
Phone Number		Fax Number				
Email Address			-			
Additional Assignee D	ata may be generated wi	thin this form by selecting the Ac	dd			

Signature:

A signature of the applicant or representative is required in accordance with 37 CFR 1.33 and 10.18. Please see 37 EFS FR 1.4(d) for the form of the signature.

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Application Da	ata Sheet 37 CFR 1.76	Attorney Docket Number	039.0075
Application Da	ita Sheet 37 CFR 1.76	Application Number	10/598,934
Title of Invention	III Nitride Semiconductor Crys Manufacturing Method Thered		Thereof, III Nitride Semiconductor Device and

Signature	/James Judge/		Date (YYYY-MM-DD)	2009-03-23	
First Name	James	Last Name	Judge	Registration Number	42,701

This collection of information is required by 37 CFR 1.76. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 23 minutes to complete, including gathering, preparing, and submitting the completed application data sheet form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.